

AN 1983:202934 HCAPLUS
DN 98:202934
TI Copper alloys as lead-frame materials of semiconductor devices
PA Sumitomo Electric Industries, Ltd., Japan
SO Jpn. Tokkyo Koho, 4 pp.
CODEN: JAXXAD
DT Patent
LA Japanese
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
	-----	----	-----	-----	-----
PI	JP 57056215	B4	19821129	JP 1977-4007	19770119
PRAI	JP 1977-4007		19770119		
AB	Cu alloys containing 0.02-0.3% Ag and 0.03-0.3% Sn (with Ag + Sn 0.1-0.5%) are used as packaged lead-frame materials for semiconductor devices. Thus, cast ingot (140 + 140 + 2000 mm) of Cu alloy [85759-48-4] containing 0.11 Sn and 0.15% Ag was hot-rolled to a 8 mm thick plate, cold-rolled, internally softened, and cold-rolled to sheet 0.6 mm thick. The sheet was annealed 3 h at 420°, and temper-rolled to 0.4 mm thickness. This sheet had thermal expansion coefficient 1.77 + 10-5/degree, tensile strength 36.5 kg/mm2, and elec. conductivity 89% of International Annealed Cu Standard				
